

1SS375

Schottky Barrier Diode

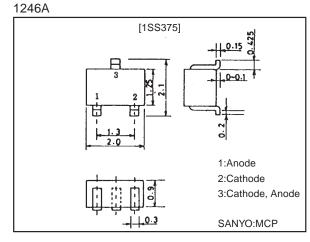
VHF, UHF Detector and Mixer Applications

Features

- Series connection of 2 elements in a very small-sized package facilitates high-density mounting and permits 1SS375-applied equipment to be made smaller.
- · Small interterminal capacitance.
- · Low forward voltage.
- · High breakdown voltage.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

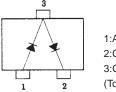
Parameter	Symbol	Conditions	Ratings	Unit
Reverse Voltage	VR		10	V
Forward Current	١ _F		35	mA
Junction Temperature	Tj		125	°C
Storage Temperature	Tstg		-55 to +125	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V _F (1)	I _F =1mA	350		420	mV
	V _F (2)	I _F =10mA	480		580	mV
Forward Current	١ _F	V _F =1V	35			mA
Reverse Current	I _R (1)	V _R =2V			0.2	μΑ
	I _R (2)	V _R =10V			10	μA
Interterminal Capacitance	С	V _R =0V, f=1MHz			0.85	pF
Forward Voltage Difference	ΔV_F	I _F =10mA			10	mV
Interterminal Capacitance Difference	ΔC	V _R =0V, f=1MHz			0.1	pF

· Marking:FH

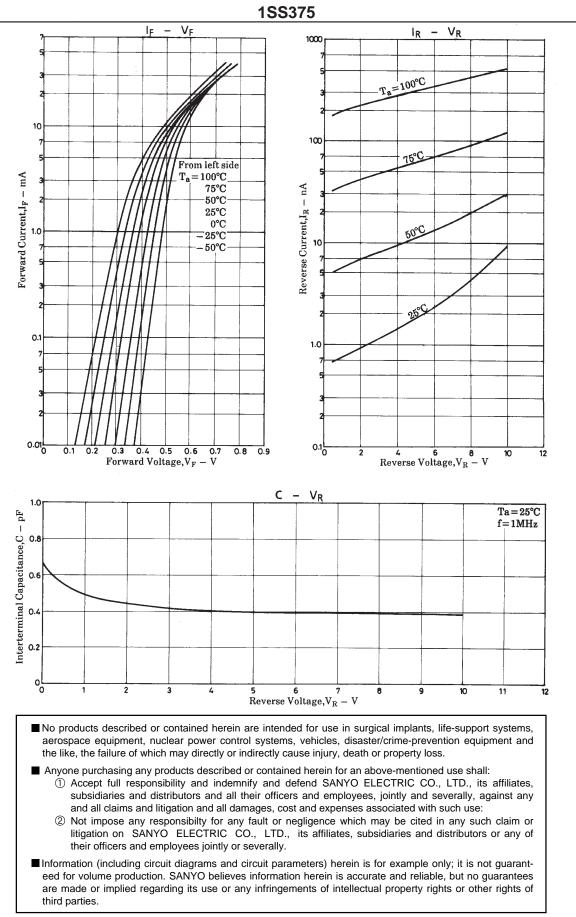
Electrical Connection



1:Anode 2:Cathode 3:Cathode, Anode (Top view)

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